



# 安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

S2ABF-S2MBF

## SMBF General Purpose Rectifier Diode 通用整流二极管

### ■Features 特点

Low forward voltage drop 低正向压降  
 Low reverse leakage current 低反向漏电流  
 High surge current capability 高浪涌电流能力  
 Surface mount device 表面贴装器件  
 Case 封装:SMBF



### ■Maximum Rating 最大额定值

( $T_A=25^{\circ}\text{C}$  unless otherwise noted 如无特殊说明, 温度为  $25^{\circ}\text{C}$ )

Characteristic 特性参数	Symbol 符号	S2 ABF	S2 BBF	S2 DBF	S2 GBF	S2 JBF	S2 KBF	S2 MBF	Unit 单位
Peak Reverse Voltage 反向峰值电压	$V_{RRM}$	50	100	200	400	600	800	1000	V
DC Reverse Voltage 直流反向电压	$V_R$	50	100	200	400	600	800	1000	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	35	70	140	280	420	560	700	V
Forward Rectified Current 正向整流电流	$I_F$	2							A
Peak Surge Current 峰值浪涌电流	$I_{FSM}$	60							A
Thermal Resistance Junction-Lead 结到管脚热阻	$R_{\theta JL}$	16							$^{\circ}\text{C}/\text{W}$
Junction and Storage Temperature 结温和储藏温度	$T_J, T_{stg}$	150 $^{\circ}\text{C}$ , -55to+150 $^{\circ}\text{C}$							

### ■Electrical Characteristics 电特性

( $T_A=25^{\circ}\text{C}$  unless otherwise noted 如无特殊说明, 温度为  $25^{\circ}\text{C}$ )

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位	Test Condition 测试条件
Forward Voltage 正向电压	$V_F$		1.0	1.1	V	$I_F=2\text{A}$
Reverse Current( $T_A=25^{\circ}\text{C}/$ ) 反向电流( $T_A=125^{\circ}\text{C}/$ )	$I_R$			5 200	$\mu\text{A}$	$V_R=V_{RRM}$
Diode Capacitance 二极管电容	$C_D$		30		pF	$V_R=4\text{V}, f=1\text{MHz}$

## ■ Typical Characteristic Curve 典型特性曲线

FIG.1-TYPICAL FORWARD CHARACTERISTICS

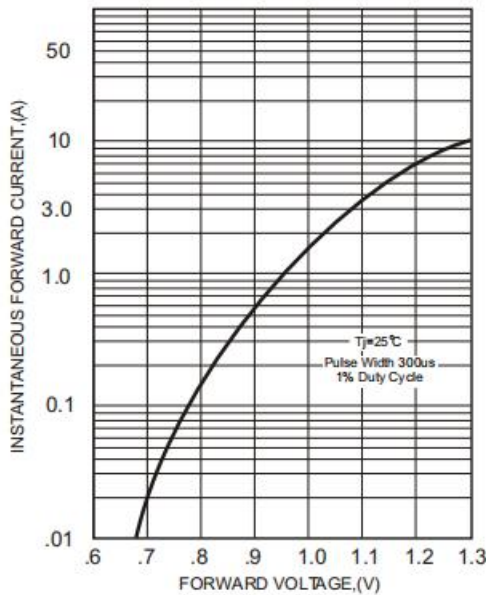


FIG.2-TYPICAL FORWARD CURRENT DERATING CURVE

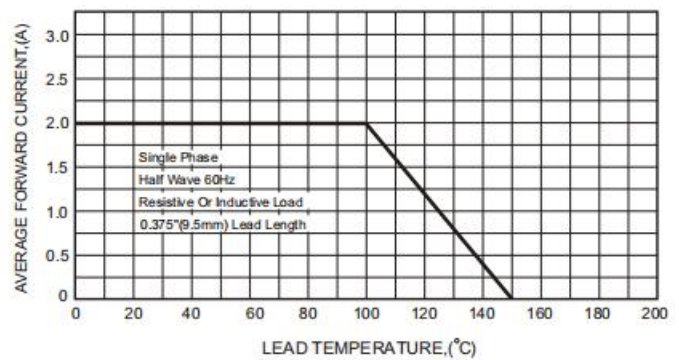


FIG.4-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

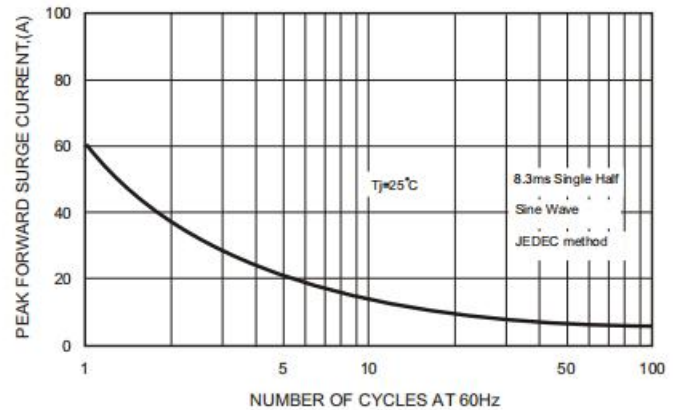


FIG.3 - TYPICAL REVERSE CHARACTERISTICS

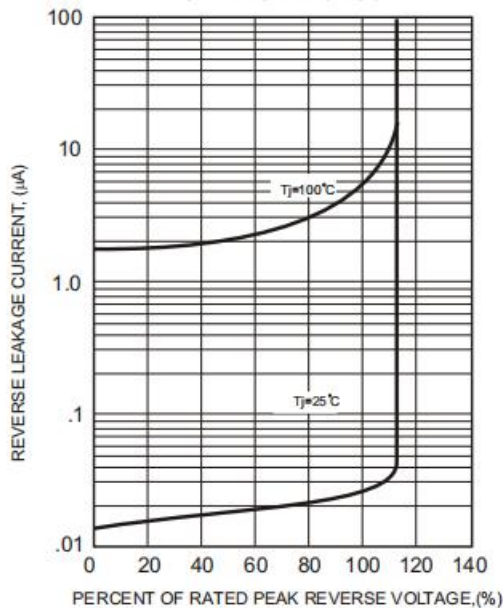
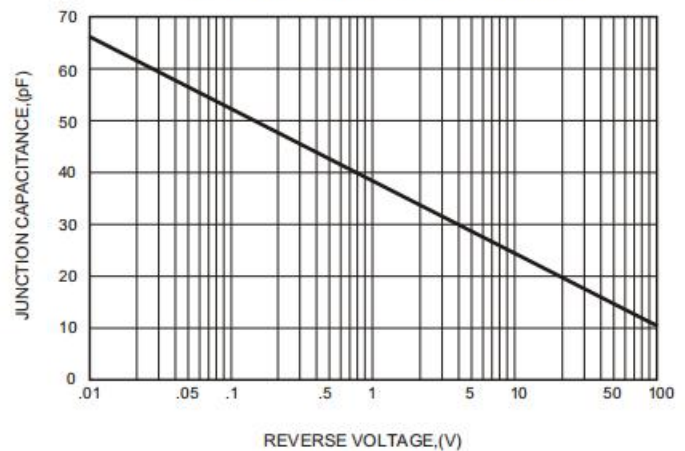
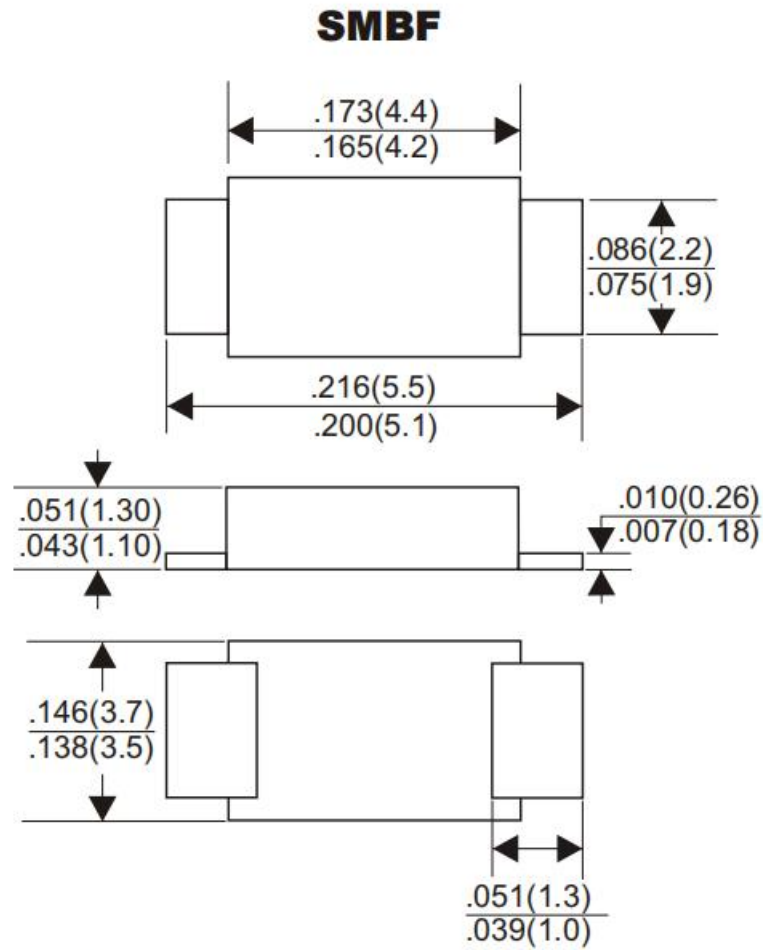


FIG.5-TYPICAL JUNCTION CAPACITANCE



■Dimension 外形封装尺寸



Dimensions in inches and (millimeters)